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Vishay Semiconductors

650 V Gen 3 Power SiC Merged PIN Schottky Diode, 2 A



Cathode O Anode

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS						
I _F ⁽²⁾	2 A					
V _R	650 V					
V _F at I _F at 25 °C, typ.	1.30 V					
T _J max.	175 °C					
I _R at V _R at 175 °C	2.0 μA					
Q _C (V _R = 800 V)	7.2 nC					
Package	SlimSMA HV (DO-221AC)					
Circuit configuration	Single					

FEATURES

- Minimum creepage distance 3.2 mm guaranteed by design
- Comparative Tracking Index: CTI ≥ 600
- High CTI molding compound provides excellent HALOGEN FREE electrical insulation at relevant working voltages
- Positive V_F temperature coefficient for easy paralleling
- Virtually no recovery tail and no switching losses
- Temperature invariant switching behavior
- 175 °C maximum operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- · MPS structure for high ruggedness to forward current surge events
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

Wide band gap SiC based 650 V Schottky diode, designed for high performance and ruggedness.

Optimized for extreme high-speed hard switching over a wide temperature range. It is suited for demanding applications, such as bootstrap and anti-parallel diodes in AC/DC and DC/DC converters.

MECHANICAL DATA

Case: SlimSMA HV (DO-221AC)

Molding compound meets UL 94 V-0 flammability rating Base P/N-M3 - halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002

MAXIMUM RATINGS (T _A = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage	V _{RRM}		650	V			
Continuous forward current	١ _F	T _M = 140 °C (DC) ⁽¹⁾	2	А			
DC blocking voltage	V _{DC}		650	V			
Repetitive peak forward current	I _{FRM}	T_{M} = 25 °C, f = 50 Hz, square wave, DC = 25 $\%$	8				
Non-repetitive peak forward surge current	I _{FSM}	$T_M = 25 \text{ °C}, t_p = 10 \text{ ms}, \text{ half sine wave}$	16.5	А			
		T _M = 110 °C, t _p = 10 ms, half sine wave	14				
	P _{tot} ⁽¹⁾	T _M = 25 °C	12.5	w			
Power dissipation	Ftot ("	T _M = 110 °C	5.4	~~~			
	P _{tot} ⁽²⁾	T _M = 25 °C	9.7	w			
		T _M = 110 °C	4.2	7 ^{vv}			
121	∫i ² dt	T _M = 25 °C	1.4	A2.			
l ² t value		T _M = 110 °C	1.0	A ² s			
Operating junction and storage temperatures	T _J ⁽³⁾ , T _{Stg}		-55 to +175	°C			

Notes

(1) Based on typical Rth

⁽²⁾ Based on maximum R_{th}

 $^{(3)}$ The heat generated must be less than the thermal conductivity from junction-to-ambient: $dP_D/dT_1 < 1/R_{0.IA}$

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Forward voltage	V _F	I _F = 2 A	-	1.30	1.50	v	
		I _F = 2 A, T _J = 150 °C	-	1.45	1.70		
		I _F = 2 A, T _J = 175 °C	-	1.50	-		
Reverse leakage current	I _R	V _R = V _R rated	-	0.1	15	μΑ	
		$V_R = V_R$ rated, $T_J = 150 \ ^\circ C$	-	0.5	30		
		$V_{R} = V_{R}$ rated, $T_{J} = 175 \text{ °C}$	-	2.0	-		
Total capacitance	С	V _R = 1 V, f = 1 MHz	-	100	-	- pF	
		V _R = 400 V, f = 1 MHz	-	12.5	-		
Total capacitive charge	Q _C	V _R = 400 V, f = 1 MHz	-	7.2	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS (T _A = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Thermal resistance, junction to mount	R _{thJM} ⁽¹⁾		-	12	15.5	°C/W	
Marking device				C2	207		

Note

⁽¹⁾ Thermal resistance junction-to-mount follows JEDEC[®] 51-14 transient dual interface test method (TDIM)

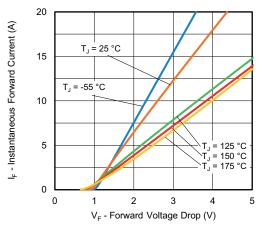


Fig. 1 - Typical Forward Voltage Drop Characteristics

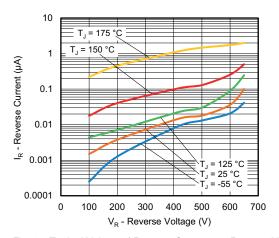


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

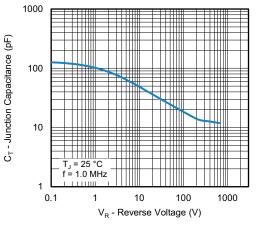


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

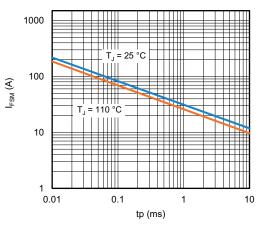


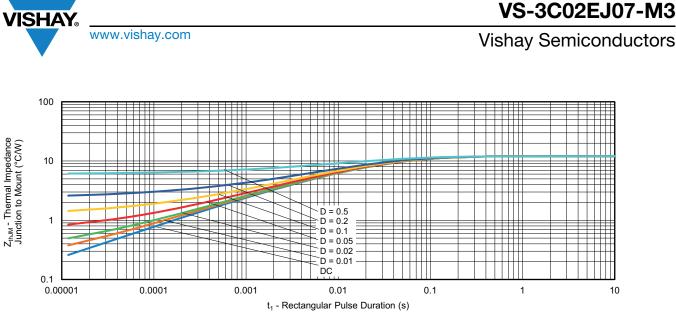
Fig. 4 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration (Square Wave)

Revision: 25-Nov-2024

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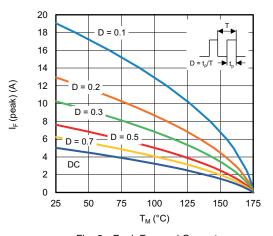


Fig. 6 - Peak Forward Current vs. Maximum Allowable Mount Temperature

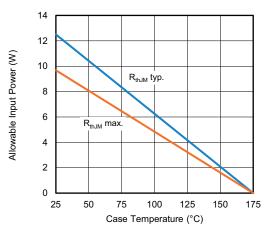


Fig. 7 - Forward Power Loss Characteristics

3 2.5 Capacitive Energy (µJ) 2 1.5 1 T_{.1} = 25 °C 0.5 . CVdV $E_J =$ 0 0 100 200 300 400 500 600 700 Reverse Voltage (V)

Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage

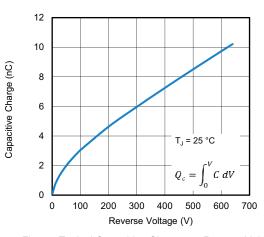


Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage

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ORDERING INFORMATION TABLE

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Device code	VS-	3C	02	E	J	07	-M3		
		2	3	4	5	6	7		
	1	- Vishay Semiconductors product							
	2	- 3C	3C = SiC diode, generation 3						
	3	- Cui	Current rating $(02 = 2 \text{ A})$						
	4	- E=	single o	diode					
	5	- J=	J = SlimSMA HV package						
	6	- Vol	Voltage rating: (07 = 650 V)						
	7	- Env	Environmental digit:						
		-M	-M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free						

 ORDERING INFORMATION

 PREFERRED P/N
 UNIT WEIGHT (g)
 BASE QUANTITY
 PACKAGING DESCRIPTION

 VS-3C02EJ07-M3/H
 0.032
 3500 per reel
 7" diameter plastic tape and reel

 VS-3C02EJ07-M3/I
 0.032
 14 000 per reel
 13" diameter plastic tape and reel

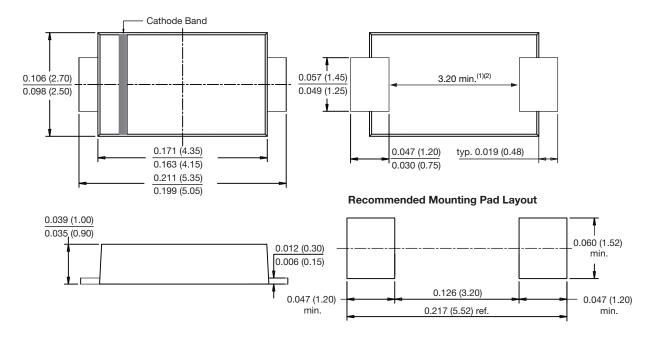
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?97278				
Part marking information	www.vishay.com/doc?98699				
Packaging information	www.vishay.com/doc?98714				



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SlimSMA HV (DO-221AC)

DIMENSIONS in inches (millimeters)



Notes

- ⁽¹⁾ Minimum creepage distance is defined and guaranteed by design
- ⁽²⁾ For high voltage applications, end users should consider the relevant guidelines and normative on creepage and clearance distances between device terminals and PCB pads.



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Revision: 01-Jan-2025

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